

EASt: [10782916 isomer memory.wsp:1]

FileViewEditToolsWindowHelp

Drafts

BRS:  
BRS:  
BRS:  
BRS: knall  
BRS: 19 21 23  
BRS: 32with 33

Pending

Active

L10: (2880230) molecu\$4 isomer\$7 organic polymer  
L11: (6146155) electric\$4 voltage potential  
L12: (2045) 10 near memory  
L13: (3253431) light radiat\$4  
L14: (185663) eras\$4  
L15: (3083) 11 with 13 with 14  
L16: (1) 12 same 15  
L17: (9) 12 and 15  
L18: (9) 17 and 14  
L19: (5455) 10 near 5 memory  
L20: (9) 19 same 15  
L21: (47) 19 and 15  
L22: (6872) (257/295,296,40,431).CCLS  
L23: (20) 15 and 22

Failed

Saved

S2: (1) 09/948877  
C2: (1) 09/948877

DBs: US:PGPUB,USPAT,EPO,JPO,DERWENT,ISW,TDB

Default operator: OR

15 and 22

Jan 2005

BRS form

ISAR form

Image

Text

HTML

	U	Inventor	Document#	Issue	P	Title	Current	Current XR	Retrieval	S	C	P	Image	Doc	P
1		Stasiak, Jam	US 682888	2004:2		Memory device having a semiconducting poly	257/777;257/237;							US 682888	
2		Krieger, Juri	US 2004015	20040:2		Memory device	257/40							US 2004015	
3		Stasiak, Jam	US 2003023	20031:2		Memory device having a semiconducting poly	257/40							US 2003023	
4		Eitan, Boaz	US 2003020	20031:2		Non-volatile electrically erasable and progra	257/296;257/E21.21							US 2003020	
5		Bohmer, Mar	US 2001000	20010:6		Semiconductor device comprising a security	257/879;257/431							US 2001000	
6		Eitan, Boaz	US 6803299	20041:2		Non-volatile electrically erasable and progra	439/593;257/296							US 6803299	
7		Peng, Jack Z	US 6798693	20040:2		Semiconductor memory cell and memory arr	365/177;257/296							US 6798693	
8		Peng, Jack Z	US 6766980	20040:2		Smart card having memory using a breakdown	235/492;257/296							US 6766980	
9		Peng, Jack Z	US 6700151	20040:2		Reprogrammable non-volatile memory using a	257/299;257/253							US 6700151	
10		Jiang, Chun e	US 6600188	20030:6		EEPROM with a neutralized doping at tunnel	257/296;257/549;							US 6600188	

FileDetailsHTML

Ready

3/2/04